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The invention relates to semiconductor material production processes and can be used in semiconductor technology. The process, according to the invention, consists in sintering ZnO powder by means of chemical transport reaction method in a closed volume at a sintering temperature of 900...150°C. As transport agents are used HCl with an initial pressure of 1...6 atm, hydrogen with an initial pressure of 50...200% of the HCl pressure, and carbon in the amount necessary to meet the condition $C:HCl=0...1$ mol.

Claims: 1

Fig.: 2